

GP1S53V/GP1S58V

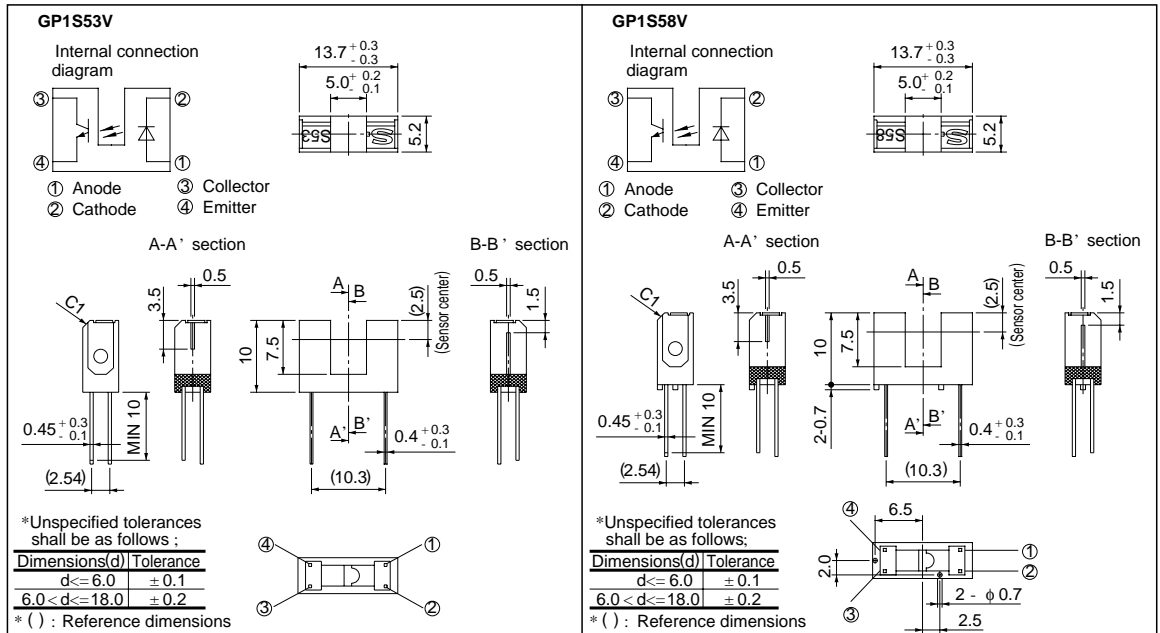
Compact Photointerrupter

■ Features

1. Compact type
2. High sensing accuracy (Slit width : 0.5mm)
3. PWB direct mounting type
4. With positioning pin (GP1S58V)

■ Outline Dimensions

(Unit : mm)



■ Absolute Maximum Ratings (Ta = 25°C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I_F	50	mA
	*1 Peak forward current	I_{FM}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation	P	75	mW
Output	Collector-emitter voltage	V_{CEO}	35	V
	Emitter-collector voltage	V_{ECO}	6	V
	Collector current	I_C	20	mA
	Collector power dissipation	P_C	75	mW
	Operating temperature	T_{opr}	- 25 to + 85	°C
	Storage temperature	T_{stg}	- 40 to + 100	°C
	*2 Soldering temperature	T_{sol}	260	°C

*1 Pulse width $\leq 100 \mu s$, Duty ratio = 0.01

*2 For 5 seconds

■ Electro-optical Characteristics

($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input	Forward voltage	V_F	$I_F = 20\text{mA}$	-	1.25	1.4	V	
	Peak forward voltage	V_{FM}	$I_{FM} = 0.5\text{A}$	-	3	4	V	
	Reverse current	I_R	$V_R = 3\text{V}$	-	-	10	μA	
Output	Collector dark current	I_{CEO}	$V_{CE} = 20\text{V}$	-	1	100	nA	
Transfer characteristics	Collector Current	I_c	$I_F = 20\text{mA}, V_{CE} = 5\text{V}$	0.5	-	1.5	mA	
	Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_F = 40\text{mA}, I_C = 0.2\text{mA}$	-	-	0.4	V	
	Response time	Rise time	t_r	$V_{CE} = 2\text{V}, I_C = 2\text{mA}$	-	3	15	μs
		Fall time	t_f	$R_L = 100\Omega$	-	4	20	μs

Fig. 1 Forward Current vs. Ambient Temperature

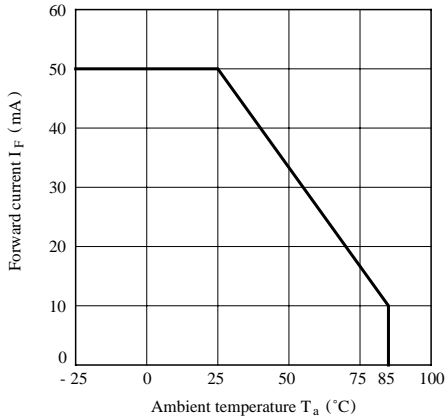


Fig. 2 Collector Power Dissipation vs. Ambient Temperature

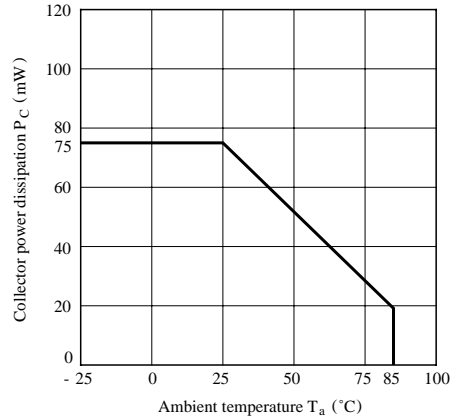


Fig. 3 Peak Forward Current vs. Duty Ratio

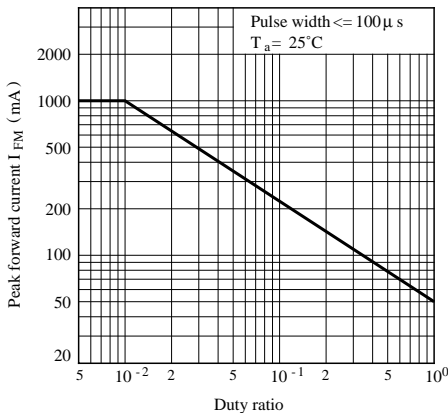


Fig. 4 Forward Current vs. Forward Voltage

